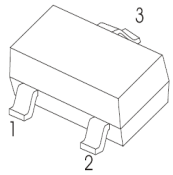
TRANSISTOR(PNP)

SOT－23



1. BASE
2. EMITTER
3. COLLECTOR

FEATURES

- Low Collector Current
- Low Collector Power Dissipation

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current	-200	mA
P_C	Collector Power Dissipation	200	mW
$R_{\Theta JA}$	Thermal Resistance From Junction To Ambient	625	℃/W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55～+150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-100μA, I_E=0	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-0.1mA, I_B=0	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-100μA, I_C=0	-6			V
Collector cut-off current	I_{CBO}	V_{CB}=-60V, I_E=0			-100	nA
Emitter cut-off current	I_{EBO}	V_{EB}=-6V, I_C=0			-100	nA
DC current gain	$h_{FE(1)}$	V_{CE}=-6V, I_C=-1mA	150		500	
	$h_{FE(2)}$	V_{CE}=-6V, I_C=-0.1mA	90			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-100mA, I_B=-10mA			-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-100mA, I_B=-10mA			-1	V
Transition frequency	f_T	V_{CE}=-6V,I_C=-10mA		200		MHz
Collector output capacitance	C_{ob}	V_{CB}=-6V, I_E=0, f=1MHz		4		pF

CLASSIFICATION OF $h_{FE(1)}$

RANK	M·E	M·F
RANGE	150–300	250–500
MARKING	M·E	M·F